



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
40V	4.5mΩ @ V _{GS} = 10V	95A

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_a Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET has been designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

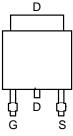
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.33 grams (Approximate)

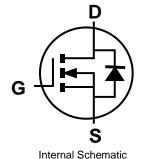




Top View



Top View Pin Out



Ordering Information (Note 5)

-			
	Part Number	Case	Packaging
	DMTH4005SK3Q-13	TO252 (DPAK)	2.500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



H4005S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7)	T _C = +25°C (Note 10)	I _D	95	А
	$T_{\rm C} = +100^{\circ}{\rm C}$ $T_{\rm C} = +25^{\circ}{\rm C}$		73	
Maximum Body Diode Forward Current (Note 7)	Is	83	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	150	Α	
Avalanche Current, L=0.1mH	I _{AS}	32.5	Α	
Avalanche Energy, L=0.1mH	Eas	52.8	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	38	°C/W	
Total Power Dissipation (Note 7)	T _C = +25°C	P _D	100	W
Thermal Resistance, Junction to Case (Note 7)	Rejc	1.5	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

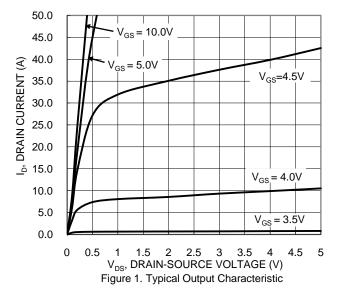
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_		V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	2		4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	3.6	4.5	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V_{SD}	_	0.9	_	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 9)					•		
Input Capacitance	C _{iss}	_	3,062	_		V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		902.2	_	pF		
Reverse Transfer Capacitance	Crss	_	179.2	_			
Gate Resistance	R_{G}		0.67	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg		49.1	_		V 00V I 50A	
Gate-Source Charge	Q_{gs}	_	10.3		nC	$V_{DD} = 20V, I_D = 50A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_{gd}	_	13	_		VGS - 10V	
Turn-On Delay Time	t _{D(ON)}	_	8.7				
Turn-On Rise Time	t _R	_	6.8			$V_{DD} = 20V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	18.6		ns	$I_D = 50A$, $R_G = 3\Omega$	
Turn-Off Fall Time	t _F	_	7.3				
Body Diode Reverse Recovery Time	t _{RR}	_	31.8		ns	I _F = 50A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	26.5	_	nC		

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.
 10. Package limited.







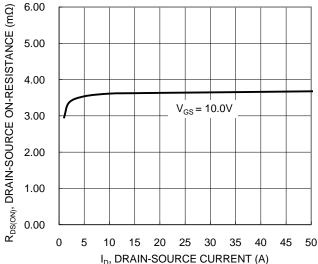


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

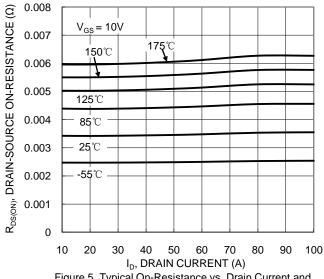
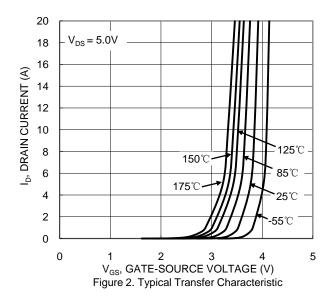
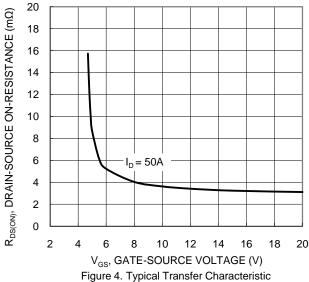


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





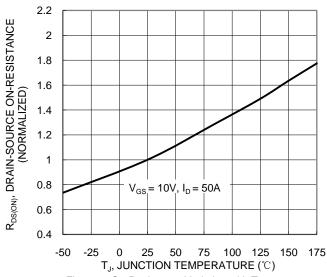


Figure 6. On-Resistance Variation with Temperature





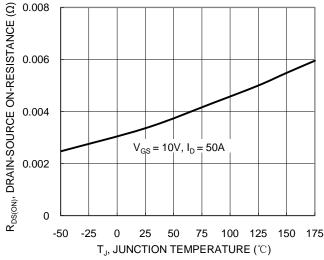


Figure 7. On-Resistance Variation with Temperature

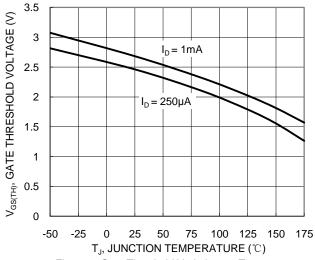


Figure 8. Gate Threshold Variation vs. Temperature

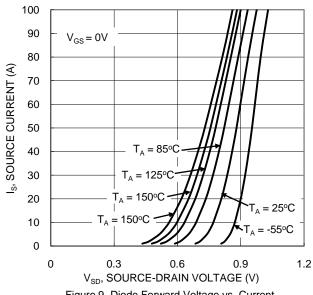
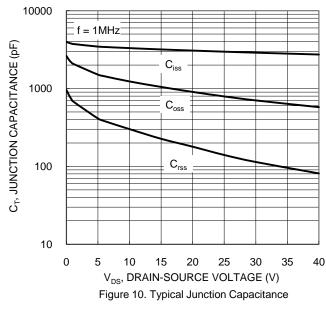
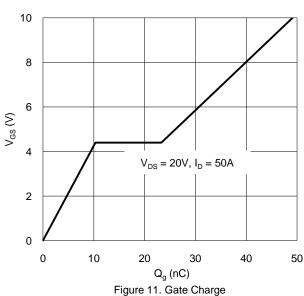


Figure 9. Diode Forward Voltage vs. Current





1000 $R_{DS(ON)}$ Limited 100 ID, DRAIN CURRENT (A) 10 $T_{J(Max)} = 175$ °C $T_C = 25$ °C Single Pulse DUT on Infinite Heatsink V_{GS}= 10V 0.1 0.1 10 100 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



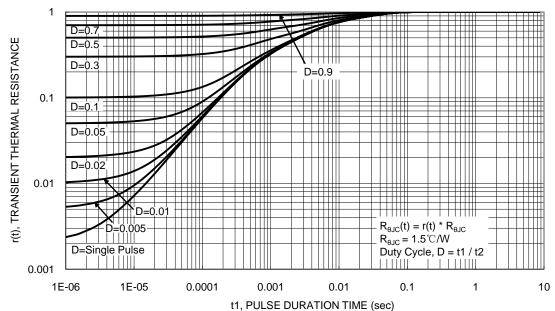
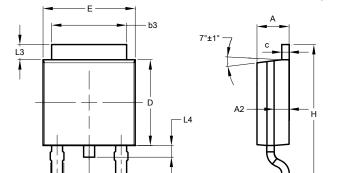


Figure 13. Transient Thermal Resistance

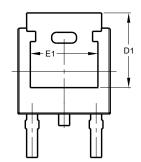


Package Outline Dimensions

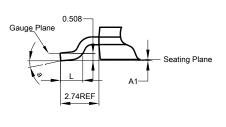
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b(3x)



- b2(2x)



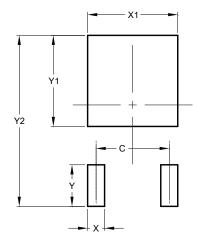
TO252 (DPAK)

TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	D1 5.21 -		-		
е		2.286			
Е	6.45	6.70	6.58		
E1	4.32		-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Υ	2.600			
Y1	5.700			
Y2	10.700			



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